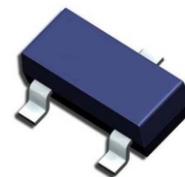


General Purpose Transistor

COMCHIP

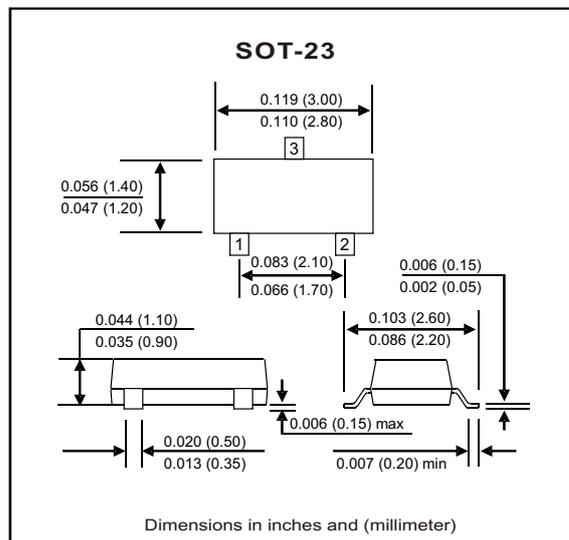
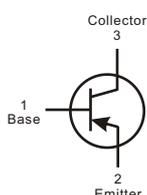
SMD Diodes Specialist

MMBT2907-G (PNP) RoHS Device



Features

- Epitaxial planar die construction
- Device is designed as a general purpose amplifier and switching.



Maximum Ratings(at TA=25°C unless otherwise noted)

Parameter	Symbol	Min	Max	Unit
Collector-Base voltage	V _{CB0}		-60	V
Power dissipation	P _{CM}		0.3	W
Collector current-Continuous	I _{CM}		-0.6	A
Storage temperature and junction temperature	T _{STG} , T _J	-55	+150	°C

Electrical Characteristics(at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Max	Unit
Collector-Base breakdown voltage	I _C =-10μA, I _E =0	V _{(BR)CBO}	-60		V
Collector-emitter breakdown voltage	I _C =-10mA, I _B =0	V _{(BR)CEO}	-40		V
Emitter-base breakdown voltage	I _E =-10μA, I _C =0	V _{(BR)EBO}	-5		V
Collector cut-off current	V _{CB} =-50V, I _E =0	I _{CBO}		-0.1	μA
Collector cut-off current	V _{CB} =-35V, I _B =0	I _{CEO}		-0.1	μA
Emitter cut-off current	V _{EB} =-3V, I _C =0	I _{EBO}		-0.1	μA
DC current gain	V _{CE} =-10V, I _C =-150mA	h _{FE(1)}	100	300	
	V _{CE} =-10V, I _C =-1mA	h _{FE(2)}	50		
Collector-emitter saturation voltage	I _C =-500mA, I _B =-50mA	V _{CE(sat)}		-1	V
Base-emitter saturation voltage	I _C =-500mA, I _B =-50mA	V _{BE(sat)}		-2	V
Transition frequency	V _{CE} =-20V, I _C =-50mA F=100MHz	f _T	200		Mhz